

Abstract of the Disclosure

Provided is a reaction chamber for depositing a thin film. The reaction chamber includes a reactor block; a wafer block located inside the reactor block; a top plate that covers the reactor block to maintain a predetermined pressure; a 5 feeding unit which supplies reactive gases to the reactor block; a shower head, which is installed in the top plate and includes a plurality of first spray holes for spraying the first reactive gas on a wafer and a plurality of second spray holes for spraying the second reactive gas; and an exhaust unit which expels gases from the reactor block. The feeding unit includes a feeding block; a distributing block; two or 10 more first gas transfer pipes; and a second gas transfer pipe. The shower head includes an upper diffusion block, an intermediate diffusion block, and a lower diffusion block.